

Fig. 1A

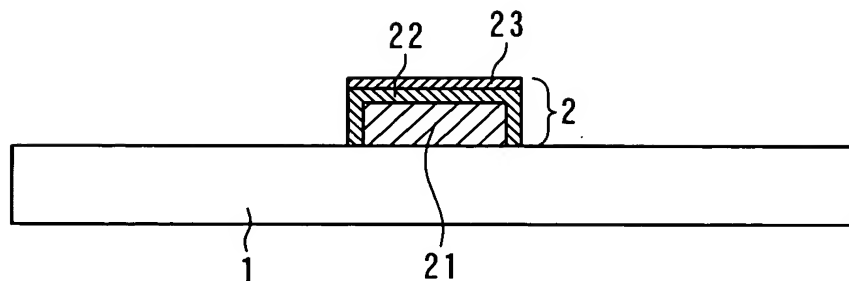


Fig. 1B

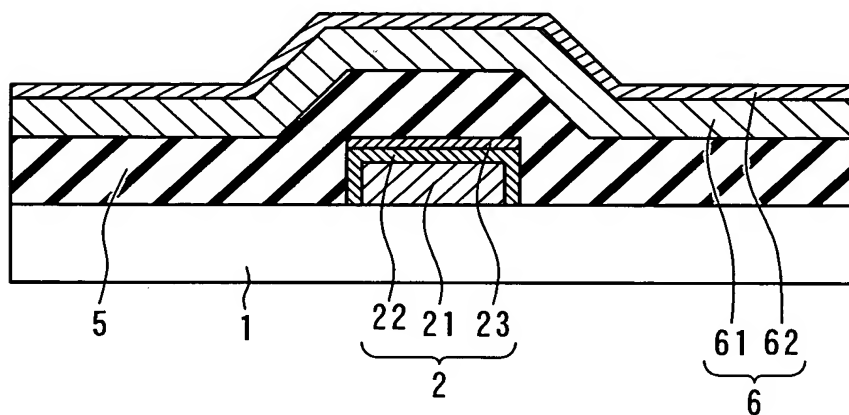


Fig. 1C

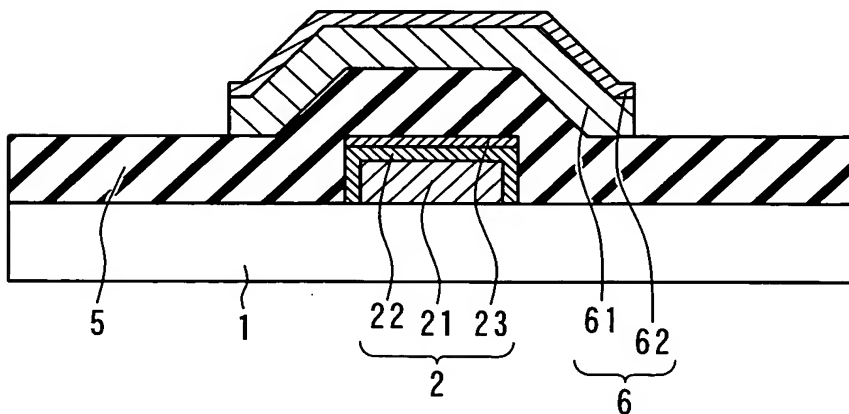


Fig. 1D

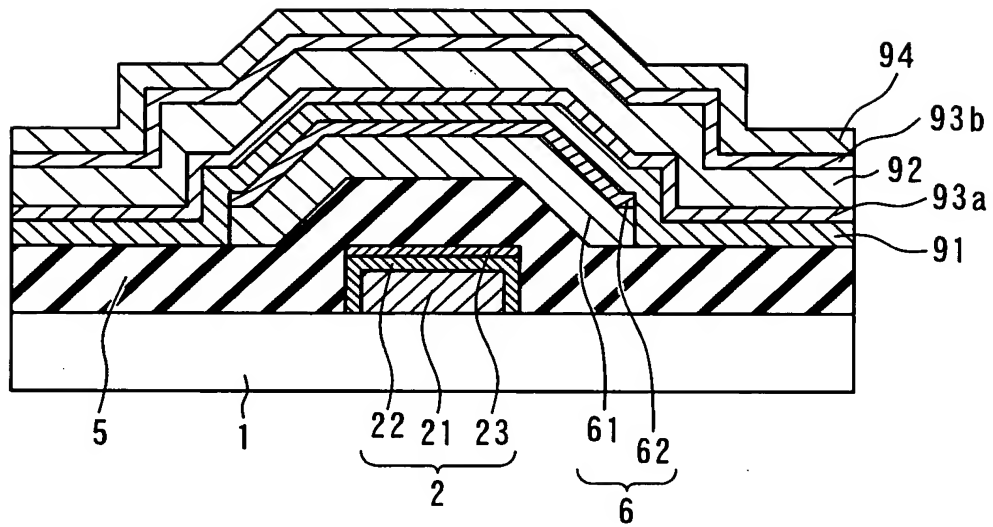


Fig. 1E

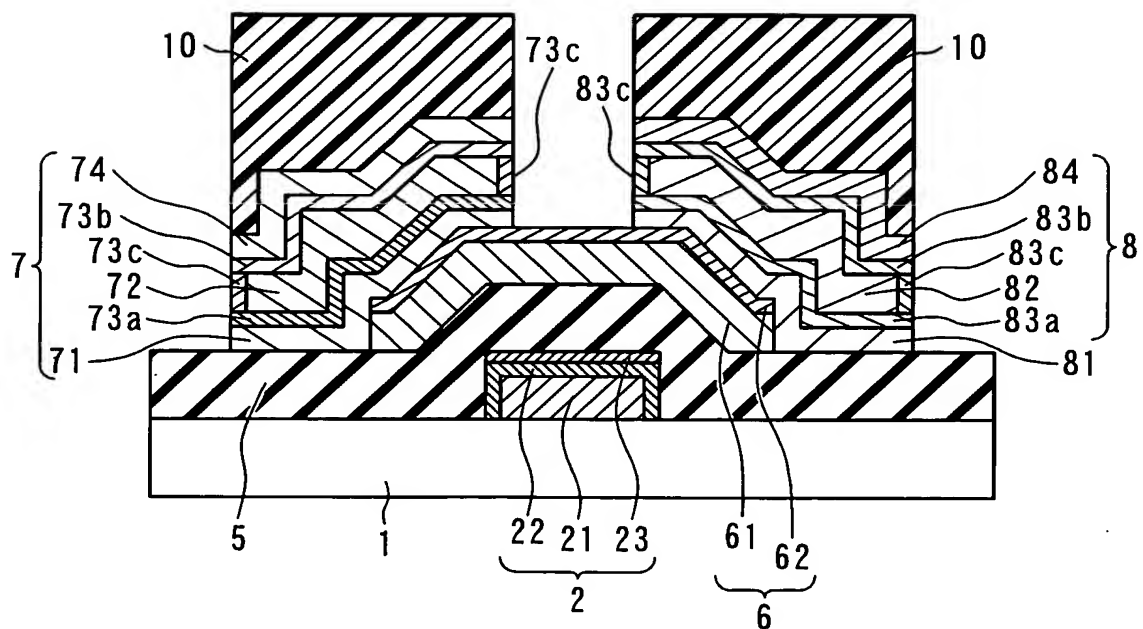


Fig. 1F

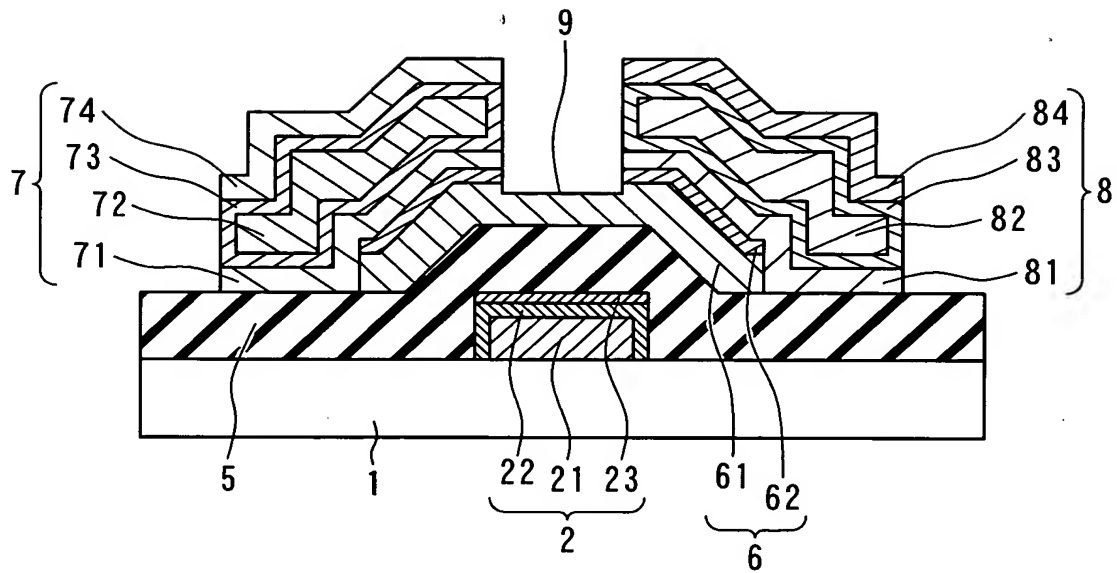


Fig. 2A

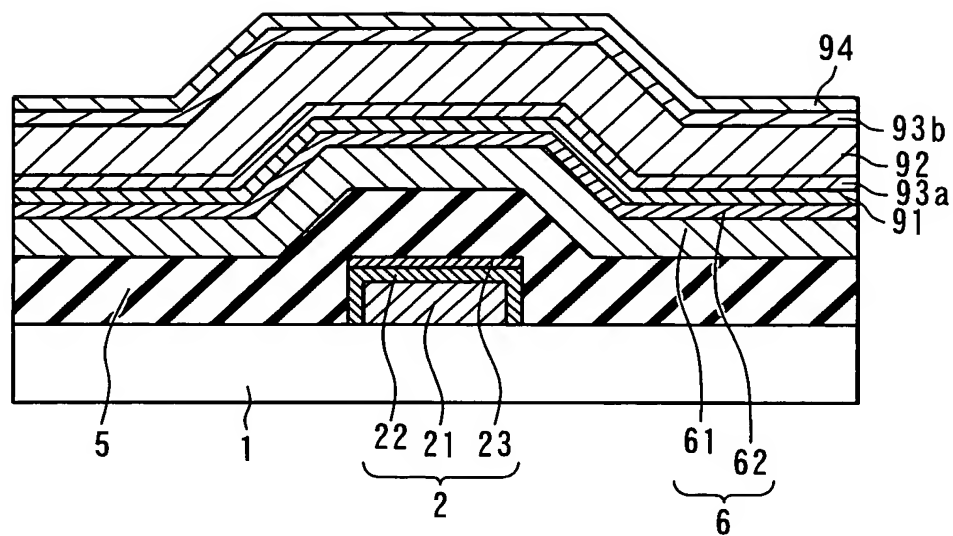


Fig. 2B

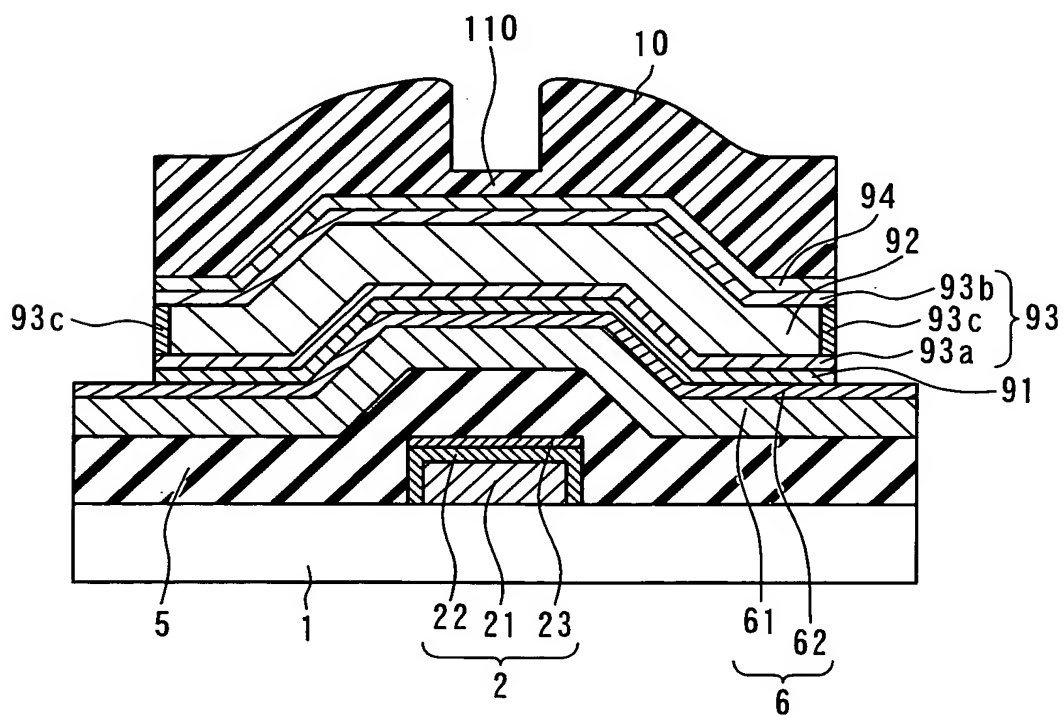


Fig. 2C

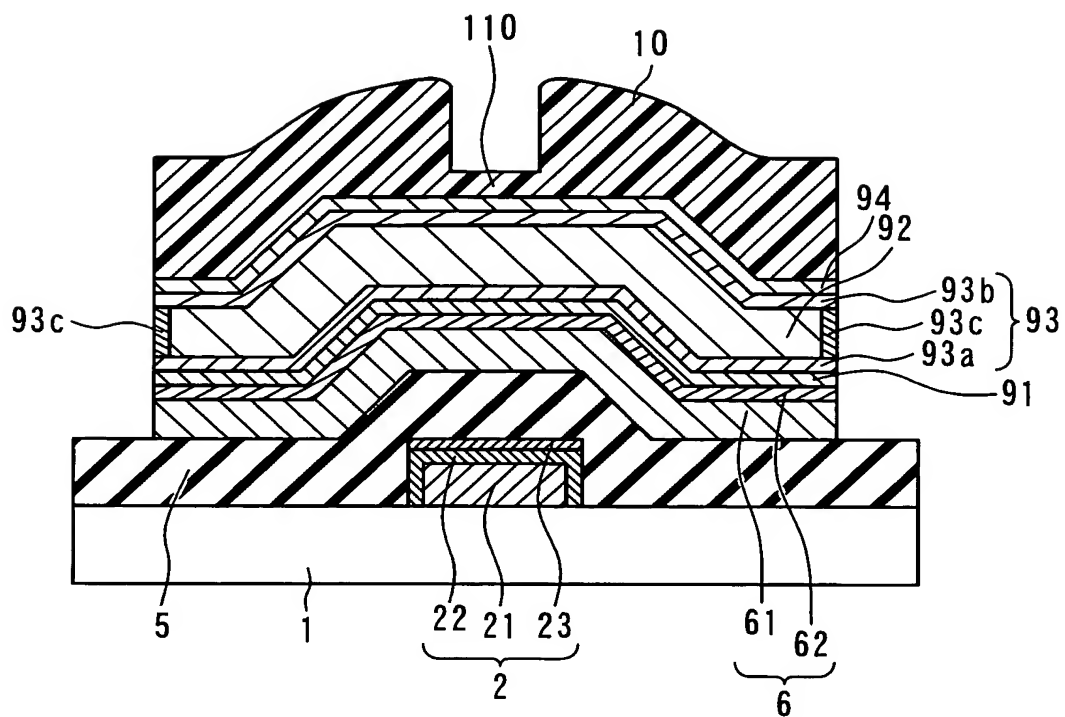
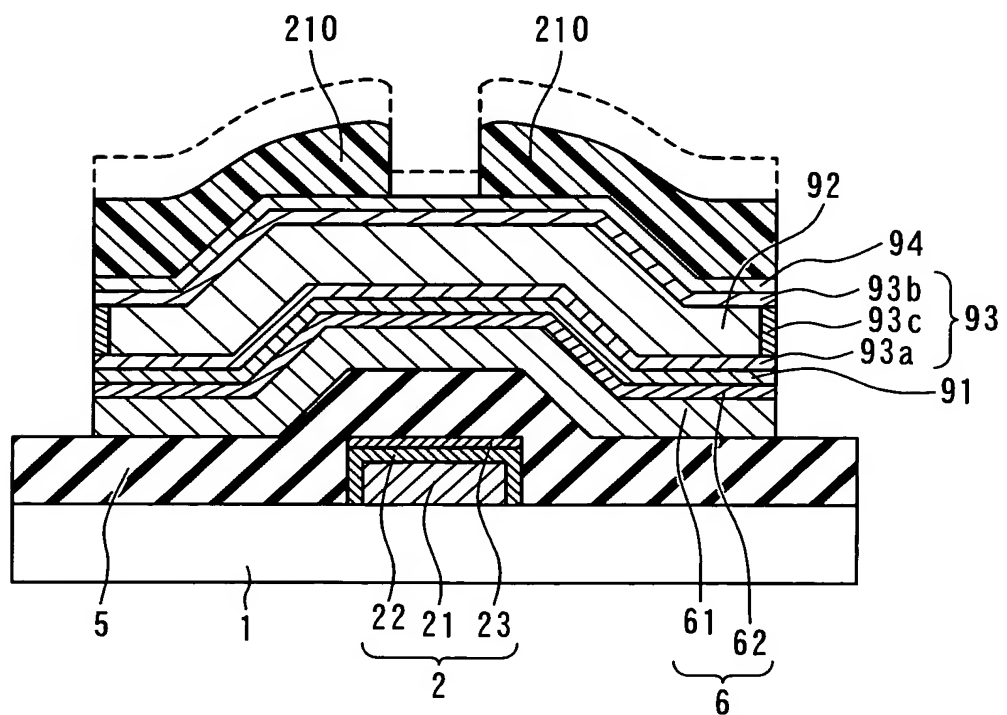


Fig. 2D



This cross-sectional diagram illustrates a semiconductor device. At the base is a substrate (1) with a layer (5). A central gate stack (2) consists of layers 21, 22, and 23. To the left and right are two transistors (7). Each transistor has a gate stack (6) with layers 61 and 62. The channel regions of the transistors are labeled 71, 72, 73, and 74. A central region between the transistors is labeled 110. Other labels include 210, 81, 82, 83a, 83b, 83c, 84, and 85.

**F i g . 2 G**

